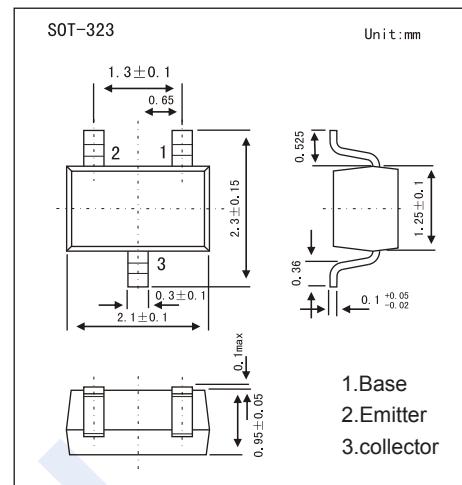


**NPN Transistors****KTC4076****■ Features**

- Excellent hFE Linearity
- Complementary to KTA2015

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CBO</sub>	35	V
Collector - Emitter Voltage	V <sub>C EO</sub>	30	
Emitter - Base Voltage	V <sub>EBO</sub>	5	
Collector Current - Continuous	I <sub>C</sub>	500	mA
Base Current	I <sub>B</sub>	50	
Collector Power Dissipation	P <sub>C</sub>	100	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

**■ Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = 100uA, I <sub>E</sub> = 0	35			V
Collector-emitter breakdown voltage	V <sub>C EO</sub>	I <sub>C</sub> = 1 mA, I <sub>B</sub> =0	30			
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = 100uA, I <sub>C</sub> = 0	5			
Collector-base cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 35V, I <sub>E</sub> = 0			0.1	uA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> =0			0.1	
Collector-emitter saturation voltage	V <sub>C E(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA			0.25	V
Base-emitter saturation voltage	V <sub>B E(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA			1.2	
Base-emitter voltage	V <sub>BE</sub>	V <sub>C E</sub> = 1V, I <sub>C</sub> =100mA			1	
DC current gain	h <sub>FE</sub>	V <sub>C E</sub> = 1V, I <sub>C</sub> =100mA	70		240	
		O V <sub>C E</sub> = 6V, I <sub>C</sub> =400mA	25			
		Y V <sub>C E</sub> = 6V, I <sub>C</sub> =400mA	40			
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 6V, I <sub>E</sub> =0, f=1MHz			7	pF
Transition frequency	f <sub>T</sub>	V <sub>C E</sub> = 6V, I <sub>C</sub> = 20mA			300	MHz

**■ Classification of hfe**

Type	KTC4076-O	KTC4076-Y
Range	70-140	120-240
Marking	WO	WY